

Hui Xiong

List of Publications by Year in descending order

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17
papers

160
citations

1307594

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1125743

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docs citations

17
times ranked

215
citing authors

#	ARTICLE	IF	CITATIONS
1	A phosphorus-doped g-C ₃ N ₄ nanosheets as an efficient and sensitive fluorescent probe for Fe ³⁺ detection. <i>Optical Materials</i> , 2021, 119, 111393.	3.6	9
2	Ru ⁴⁺ -assisted phase transition in VO ₂ nanoparticles: Electronic structures and optical properties. <i>Vacuum</i> , 2021, 192, 110495.	3.5	9
3	Luminescence and structure regulation of graphitic carbon nitride by electron rich P ions doping. <i>Journal of Luminescence</i> , 2020, 228, 117616.	3.1	9
4	Extraction of Backscattering and Absorption Coefficients of Magnetite Nanosphere Composites from Light-Scattering Measurements: Implications for Optomagnetic Sensing. <i>ACS Applied Nano Materials</i> , 2020, 3, 11172-11183.	5.0	3
5	First-principles study on stability, electronic and optical properties of Janus-functionalized ZnO monolayer and bilayer for optoelectronic device. <i>Vacuum</i> , 2020, 181, 109749.	3.5	6
6	Low temperature sintering and nonlinear dielectric properties of lithium-doped Ba _{0.6} Sr _{0.4} TiO ₃ thick films prepared by tape-casting. <i>Journal of Materials Science: Materials in Electronics</i> , 2019, 30, 3488-3494.	2.2	4
7	Temperature Insensitive Optical Fiber Laser Bend Sensor With a Low Detection Limit. <i>IEEE Photonics Technology Letters</i> , 2015, 27, 2599-2602.	2.5	14
8	Occurrence and elimination of in-plane misoriented crystals in AlN epilayers on sapphire via pre-treatment control. <i>Chinese Physics B</i> , 2014, 23, 028101.	1.4	3
9	Fabrication of low-density GaN/AlN quantum dots via GaN thermal decomposition in MOCVD. <i>Nanoscale Research Letters</i> , 2014, 9, 341.	5.7	8
10	Effect of the Al _{0.3} Ga _{0.7} As interlayer thickness upon the quality of GaAs on a Ge substrate grown by metal-organic chemical vapor deposition. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013, 31, 041202.	1.2	9
11	The Advantages of AlGaIn-Based UV-LEDs Inserted With a p-AlGaIn Layer Between the EBL and Active Region. <i>IEEE Photonics Journal</i> , 2013, 5, 1600310-1600310.	2.0	29
12	Effects of polarization on intersubband transitions of Al _x Ga _{1-x} N/GaN multi-quantum wells. <i>Chinese Physics B</i> , 2013, 22, 057302.	1.4	4
13	Effects of the V/III Ratio of a Low-Temperature GaN Buffer Layer on the Structural and Optical Properties of Al _x Ga _{1-x} N-GaN Films Grown on r-Plane Sapphire Substrates by MOCVD. <i>Chinese Physics Letters</i> , 2012, 29, 088101.	3.3	1
14	Controlled synthesis of ZnO hollow microspheres via precursor-template method and its gas sensing property. <i>Applied Surface Science</i> , 2012, 258, 8431-8438.	6.1	49
15	Improved Performance of GaN-Based Light-Emitting Diodes via AlInGaIn/InGaIn Electron-Emitting Layer. <i>Applied Physics Express</i> , 2012, 5, 112101.	2.4	1
16	Growth and properties of ZnO film grown on AlN buffer layer by PLD. , 2012, , .		1
17	The design of back surface field layer for a single GaAs solar cell. <i>Proceedings of SPIE</i> , 2009, , .	0.8	1